IXYS

HiPerFET™ Power MOSFETs

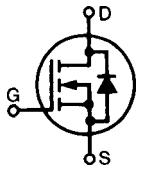
IXFH/IXFT 30N50
IXFH/IXFT 32N50

V_{DSS}	I_{D25}	$R_{DS(on)}$
500 V	30 A	0.16 Ω
500 V	32 A	0.15 Ω

$t_{rr} \leq 250$ ns

N-Channel Enhancement Mode
High dv/dt, Low t_{rr}, HDMOS™ Family

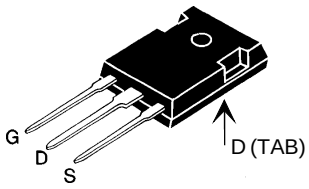
Obsolete:
IXFH30N50
IXFH32N50
IXFT32N50



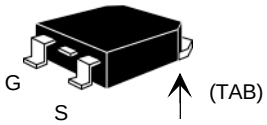
Symbol	Test Conditions		Maximum Ratings	
V_{DSS}	T_J = 25°C to 150°C		500	V
V_{DGR}	T_J = 25°C to 150°C; R_{GS} = 1 MΩ		500	V
V_{GS}	Continuous		±20	V
V_{GSM}	Transient	±30	V	
I_{D25}	T_C = 25°C	30N50	30	A
		32N50	32	A
I_{DM}	T_C = 25°C	30N50	120	A
	pulse width limited by T_{JM}	32N50	128	A
I_{AR}	T_C = 25°C	30N50	30	A
		32N50	32	A
E_{AS}	T_C = 25°C		1.5	J
E_{AR}	I_D = 25°C		45	mJ
dv/dt	$I_S \leq I_{DM}$, di/dt ≤ 100 A/µs, $V_{DD} \leq V_{DSS}$, $T_J \leq 150°C$, R_G = 2 Ω		5	V/ns
P_D	T_C = 25°C		360	W
T_J			-55 ... +150	°C
T_{JM}			150	°C
T_{stg}			-55 ... +150	°C
T_L	1.6 mm (0.062 in.) from case for 10 s		300	°C
M_d	Mounting torque		1.13/10	Nm/lb.in.
Weight			6	g

Symbol	Test Conditions		Characteristic Values (T_J = 25°C, unless otherwise specified) min.	typ.	max.	
V_{DSS}	V_{GS} = 0 V, I_D = 1 mA		500			V
	V_{DSS} temperature coefficient			0.102		%/K
$V_{GS(th)}$	$V_{DS} = V_{GS}$, I_D = 4 mA		2		4	V
	$V_{GS(th)}$ temperature coefficient			-0.206		%/K
I_{GSS}	V_{GS} = ±20 V_{DC}, V_{DS} = 0		±100			nA
I_{DSS}	V_{DS} = 0.8 • V_{DSS}	T_J = 25°C	200			µA
	V_{GS} = 0 V	T_J = 125°C			1	mA
$R_{DS(on)}$	V_{GS} = 10 V, I_D = 15A	32N50			0.15	Ω
		30N50			0.16	Ω
	Pulse test, t ≤ 300 µs, duty cycle d ≤ 2 %					

TO-247 AD (IXFH)



TO-268 (D3) Case Style



G = Gate, D = Drain,
S = Source, TAB = Drain

Features

- International standard packages
- Low $R_{DS\ (on)}$ HDMOS™ process
- Rugged polysilicon gate cell structure
- Unclamped Inductive Switching (UIS) rated
- Low package inductance
  - easy to drive and to protect
- Fast intrinsic Diode

Applications

- DC-DC converters
- Battery chargers
- Switched-mode and resonant-mode power supplies
- DC choppers
- AC motor control
- Temperature and lighting controls

Advantages

- Easy to mount with 1 screw (TO-247) (isolated mounting screw hole)
- Space savings
- High power density

IXYS reserves the right to change limits, test conditions, and dimensions.

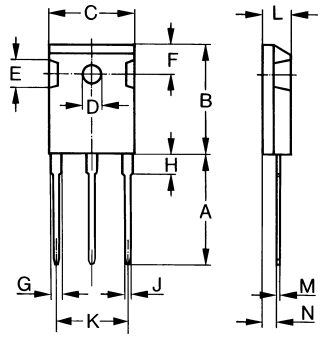
97518H (6/99)

Symbol	Test Conditions	Characteristic Values (T_J = 25°C, unless otherwise specified) min.	typ.	max.	
g_{fs}	V_{DS} = 10 V; I_D = 0.5 I_{D25}, pulse test	18	28		S
C_{iss}	V_{GS} = 0 V, V_{DS} = 25 V, f = 1 MHz	5200		5700	pF
C_{oss}		640		750	pF
C_{rss}		240		310	pF
$t_{d(on)}$	V_{GS} = 10 V, V_{DS} = 0.5 V_{DSS}, I_D = 0.5 I_{D25} R_G = 2 Ω (External)		35	45	ns
t_r			42	50	ns
$t_{d(off)}$			110	140	ns
t_f			26	35	ns
$Q_{g(on)}$	V_{GS} = 10 V, V_{DS} = 0.5 V_{DSS}, I_D = 0.5 I_{D25}		227	300	nC
Q_{gs}			29	40	nC
Q_{gd}			110	145	nC
R_{thJC}				0.35	K/W
R_{thCK}	(TO-247 Case Style)		0.25		K/W

Source-Drain Diode

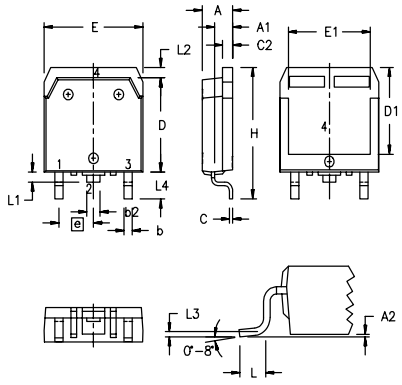
Symbol	Test Conditions		Characteristic Values (T_J = 25°C, unless otherwise specified) min.	typ.	max.	
I_S	V_{GS} = 0 V	30N50			30	A
		32N50			32	A
I_{SM}	Repetitive; pulse width limited by T_{JM}	30N50			120	A
		32N50			128	A
V_{SD}	I_F = I_S, V_{GS} = 0 V, Pulse test, t ≤ 300 µs, duty cycle d ≤ 2 %				1.5	V
t_{rr}	I_F = I_S -di/dt = 100 A/µs, V_R = 100 V	T_J = 25°C			250	ns
		T_J = 125°C			400	ns
Q_{RM}		T_J = 25°C		0.85		µC
I_{RM}		T_J = 25°C		8		A

TO-247 AD (IXFH) Outline



Dim.	Millimeter Min.	Max.	Inches Min.	Max.
A	19.81	20.32	0.780	0.800
B	20.80	21.46	0.819	0.845
C	15.75	16.26	0.610	0.640
D	3.55	3.65	0.140	0.144
E	4.32	5.49	0.170	0.216
F	5.4	6.2	0.212	0.244
G	1.65	2.13	0.065	0.084
H	-	4.5	-	0.177
J	1.0	1.4	0.040	0.055
K	10.8	11.0	0.426	0.433
L	4.7	5.3	0.185	0.209
M	0.4	0.8	0.016	0.031
N	1.5	2.49	0.087	0.102

TO-268AA (D^3 PAK)



Dim.	Millimeter Min.	Max.	Inches Min.	Max.
A	4.9	5.1	.193	.201
A_1	2.7	2.9	.106	.114
A_2	.02	.25	.001	.010
b	1.15	1.45	.045	.057
b_2	1.9	2.1	.75	.83
C	.4	.65	.016	.026
D	13.80	14.00	.543	.551
E	15.85	16.05	.624	.632
E_1	13.3	13.6	.524	.535
e	5.45 BSC		.215 BSC	
H	18.70	19.10	.736	.752
L	2.40	2.70	.094	.106
L1	1.20	1.40	.047	.055
L2	1.00	1.15	.039	.045
L3	0.25 BSC		.010 BSC	
L4	3.80	4.10	.150	.161

Min. Recommended Footprint

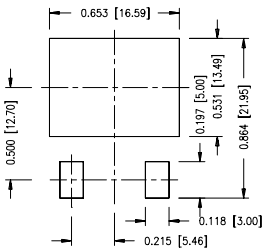


Figure 1. Output Characteristics at 25°C

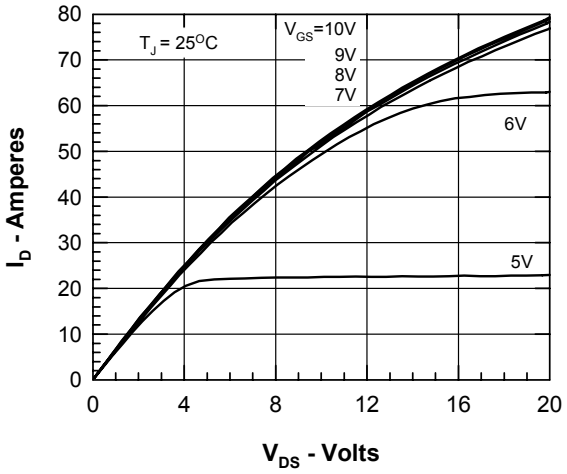


Figure 2. Output Characteristics at 125°C

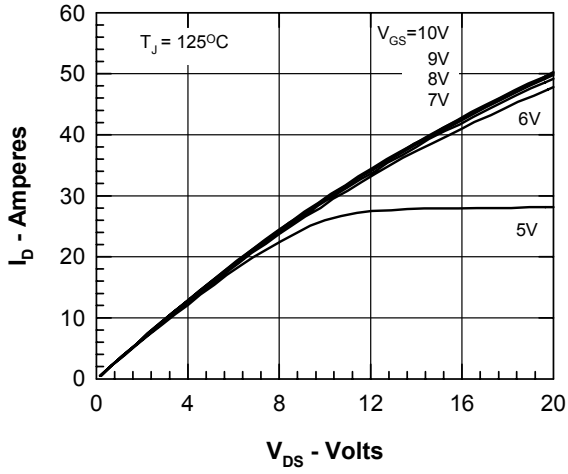


Figure 3. $R_{DS(on)}$ normalized to 15A/25°C vs. I_D

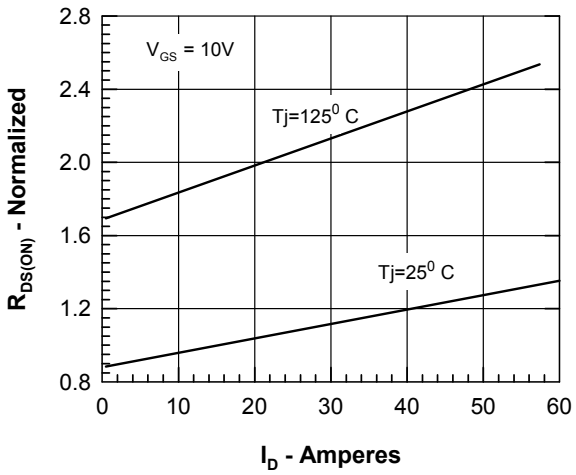


Figure 4. $R_{DS(on)}$ normalized to 15A/25°C vs. T_J

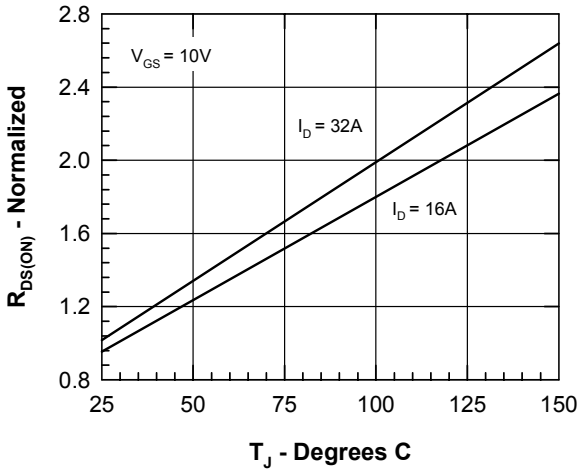


Figure 5. Drain Current vs. Case Temperature

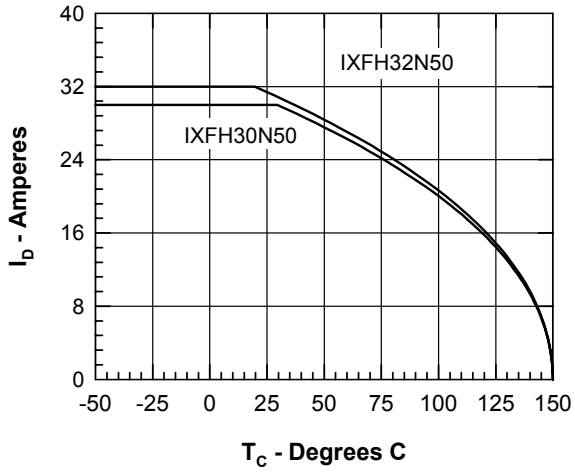


Figure 6. Admittance Curves

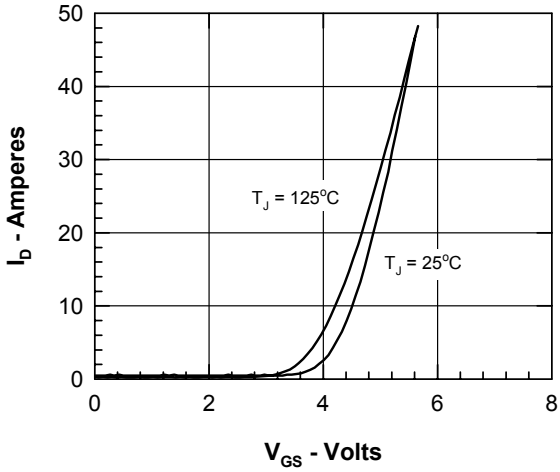


Figure 7. Gate Charge

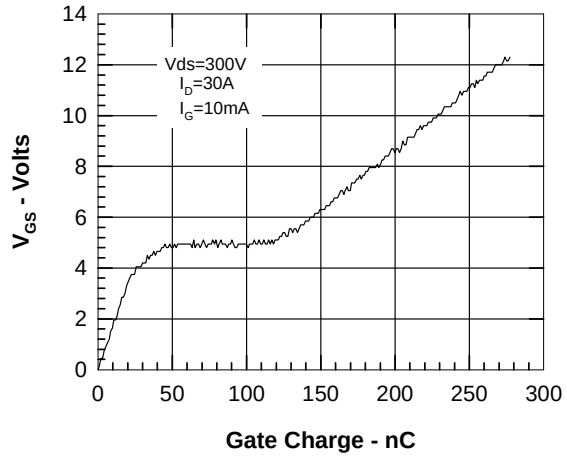


Figure 8. Capacitance Curves

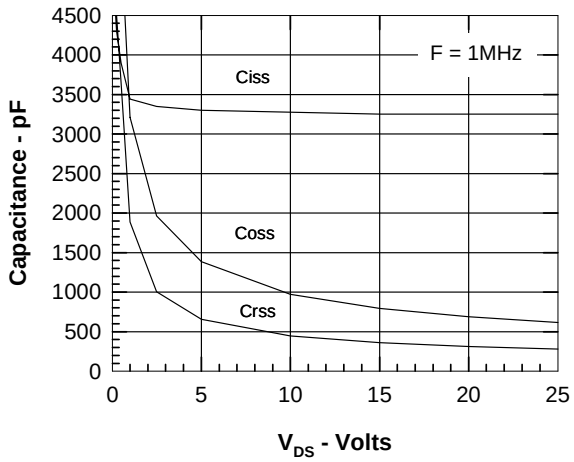


Figure 9. Forward Voltage Drop of the Intrinsic Diode

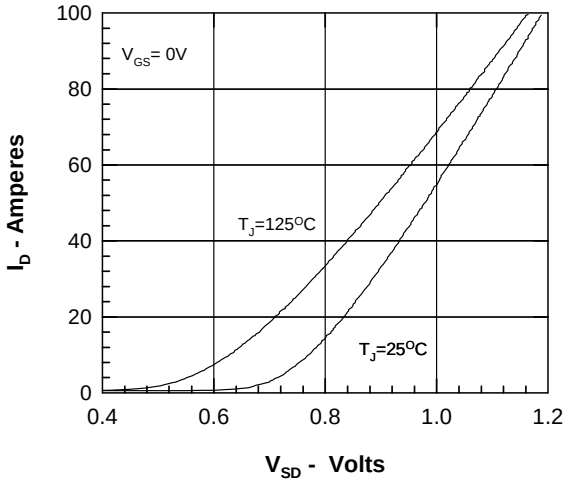


Figure 10. Transient Thermal Resistance